

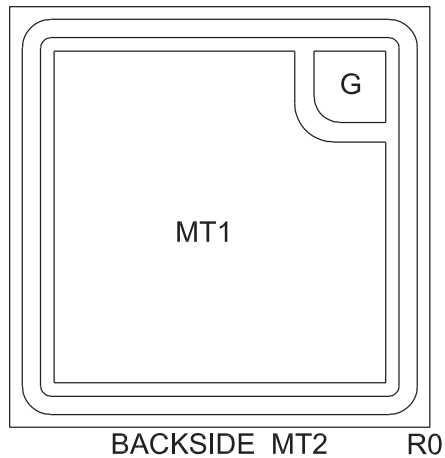
**PROCESS** CPQ166  
TRIAC  
25 Amp, 600 Volt TRIAC Chip



**PROCESS DETAILS**

Process	GLASS PASSIVATED MESA
Die Size	165 x 165 MILS
Die Thickness	9.1 MILS $\pm$ 0.4 MILS
MT1 Bonding Pad Area	134 x 100 MILS
Gate Bonding Pad Area	28 x 28 MILS
Top Side Metalization	Al - 45,000Å
Back Side Metalization	Al/Mo/Ni/Ag - 32,000Å

**GEOMETRY**



**GROSS DIE PER 4 INCH WAFER**  
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**PRINCIPAL DEVICE TYPES**  
CQDD-25M Series  
CQ220-25M Series  
CQ220-25MFP Series

R1 (29-April 2010)